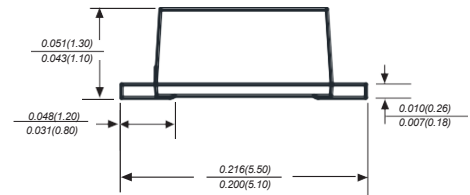
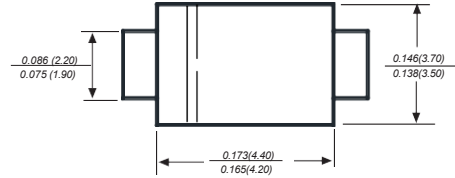


SURFACE MOUNT GENERAL PURPOSE SILICON RECTIFIER**Features**

- ◆ For surface mounted applications
- ◆ Low profile package
- ◆ Glass Passivated Chip Junction
- ◆ Easy to pick and place
- ◆ Lead free in comply with EU RoHS 2011/65/EU directives

SMBF

Dimensions in inches and (millimeters)

Maximum Ratings And Electrical Characteristics

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

Parameter	SYMBOLS	S5ABF	S5BBF	S5DBF	S5GBF	S5JBF	S5KBF	S5MBF	UNITS
Marking Code		S5AB	S5BB	S5DB	S5GB	S5JB	S5KB	S5MB	
Maximum repetitive peak reverse voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC blocking voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum average forward rectified current at $T_L=65^{\circ}C$	$I_{(AV)}$	5.0							A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	125							A
Maximum instantaneous forward voltage at 5.0A	V_F	1.10							V
Maximum DC reverse current $T_A=25^{\circ}C$ at rated DC blocking voltage $T_A=125^{\circ}C$	I_R	5.0 150.0							μA
Typical junction capacitance (NOTE 1)	C_J	45.0							pF
Typical thermal resistance (NOTE 2)	$R_{\theta JA}$	40.0							$^{\circ}C/W$
Operating junction and storage temperature range	T_J, T_{STG}	-55 to +150							$^{\circ}C$

Note: 1. Measured at 1MHz and applied reverse voltage of 4.0V D.C.

2. P.C.B. mounted with 0.5x0.5" (12.7x12.7mm) copper pad areas

Typical Characteristics

Fig.1 Forward Current Derating Curve

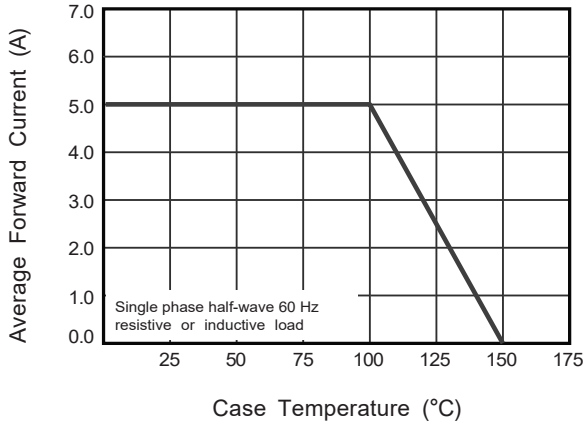


Fig.2 Typical Reverse Characteristics

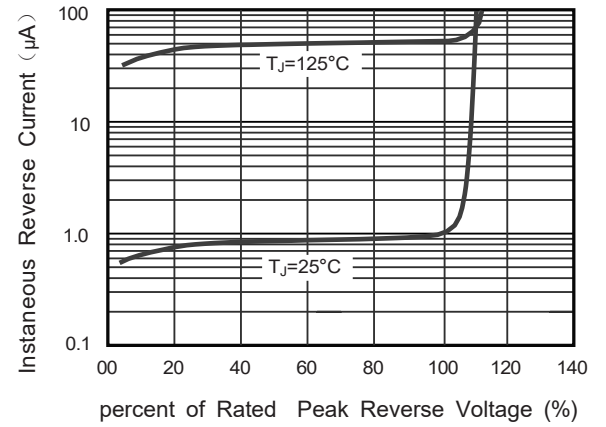


Fig.3 Typical Forward Characteristic

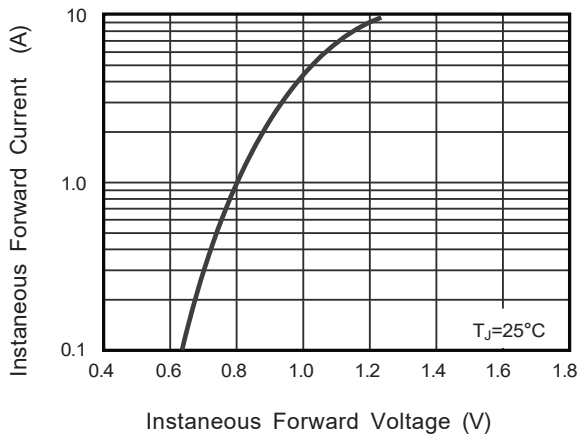


Fig.4 Typical Junction Capacitance

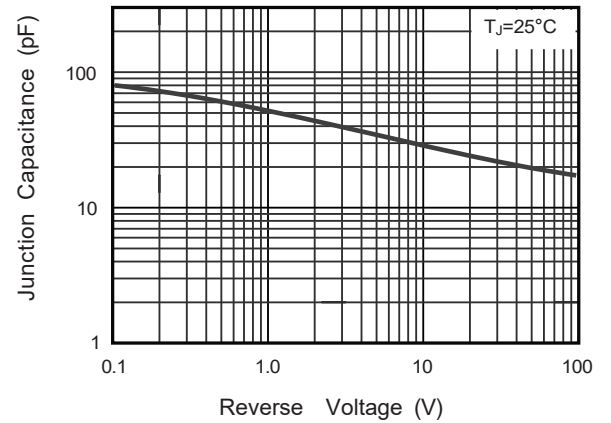
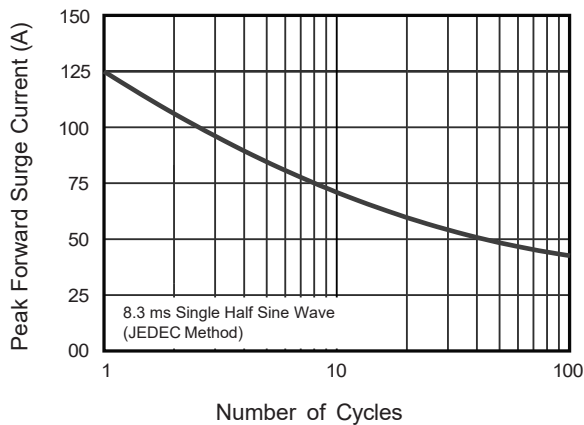


Fig.6 Maximum Non-Repetitive Peak Forward Surge Current



The curve above is for reference only.